

Table S1. Parameters and formulae used in JIP-test analysis

Parameters and formulae	Explanation of the parameters
F _o	Minimum fluorescence intensity after dark adaptation
F _j	Fluorescence intensity at J point (2 ms)
F _i	Fluorescence intensity at point I (30 ms)
F _m	Maximum fluorescence intensity after dark adaptation
F _v =F _t -F _o	Variable fluorescence intensity at t
F _v /F _m =(F _m -F _o)/F _m	Maximum photochemical efficiency of PSII
F _v /F _o =(F _m -F _o)/F _o	Potential photochemical efficiency of PSII
V _j =(F _j -F _o)/(F _m -F _o)	Fluorescence intensity at the J step
V _i =(F _i -F _o)/(F _m -F _o)	Fluorescence intensity at the I step
M _o =4(F ₃₀₀ μS-F _o)/(F _m -F _o)	Initial slope of the 0JIP fluorescence induction curve
ψ _o =E _{To} /T _{Ro} =(1-V _j)	The ratio of excitons captured in the reaction center used to push electrons to other electron receptors in the electron transport chain that exceed QA's occupation to push the QA reduced excitons
φ _{Eo} =E _{To} /ABS=[1-(F _o /F _m)]×ψ _o	Quantum yield for electron transport
φ _{Po} =T _{Ro} /ABS=1-(F _o /F _m)	Primary photochemical reaction of the largest quantum yield
ABS/CS _m ≈F _m	Light energy absorbed per unit area
T _{Ro} /CS _m =φ _{Po} (ABS/CS _m)	Light energy captured per unit area
E _{To} /CS _m =φ _{Eo} (ABS/CS _m)	Quantum yield of electron transport per unit area
D _{Io} /CS _m =(ABS/CS _m)-(T _{Ro} /CS _m)	Heat dissipation per unit area
RC/CS _m =φ _{Po} (V _j /M _o)(ABS/CS _m)	The number of reaction centers per unit area
ABS/RC=M _o (1/V _j)(1/φ _{Po})	Light energy absorbed per unit RC
T _{Ro} /RC=M _o (1/V _j)	Light energy captured per unit RC
E _{To} /RC=M _o (1/V _j)ψ _o	Quantum yield of electron transport per unit RC
PI _{abs} =(RC/ABS)[φ _{Po} /(1-φ _{Po})] [ψ _o (1-ψ _o)]	Performance index based on light energy absorption